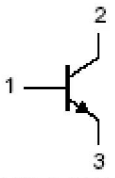
isc Silicon NPN Power Transistor BUL741

DESCRIPTION

- Collector–Emitter Breakdown Voltage
  : $V_{(BR)CEO}$ = 400V(Min.)
- Collector Saturation Voltage
  : $V_{CE(sat)}$ = 0.5V(Max) @ I_C= 0.7A

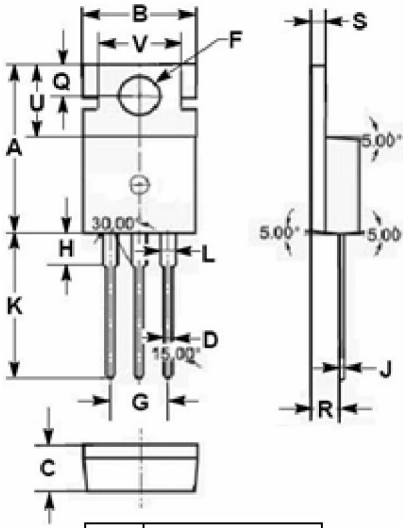
1 2 3



PIN 1. BASE
2.COLLECTOR
3. EMITTER
TO-220C package

APPLICATIONS

- Designed for electronic lamp ballast circuits switch-mode power supplies applications.



DIM	mm MIN	mm MAX
A	15.70	15.90
B	9.90	10.10
C	4.20	4.40
D	0.70	0.90
F	3.40	3.60
G	4.98	5.18
H	2.70	2.90
J	0.44	0.46
K	13.20	13.40
L	1.10	1.30
Q	2.70	2.90
R	2.50	2.70
S	1.29	1.31
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector-Emitter Voltage	1050	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	15	V
I_C	Collector Current-Continuous	2.5	A
I_{CM}	Collector Current-peak	5	A
I_B	Base Current-Continuous	1.5	A
I_{BM}	Base Current-peak	3	A
P_C	Collector Power Dissipation T_C=25℃	60	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	2.08	℃/W

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ELECTRICAL CHARACTERISTICS

T_C =25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 10mA ; I_B= 0	400	450		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 1mA; I_C= 0	15	19	24	V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 0.7A; I_B= 0.14A			0.5	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C=2A; I_B= 0.6A			1.5	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	I_C=2A; I_B= 0.6A			1.5	V
I_{CES}	Collector Cutoff Current	V_{CES}= 1050V; V_{EB}=0			10	μA
h_{FE-1}	DC Current Gain	I_C=0.1 A; V_{CE}= 5V	48		100	
h_{FE-2}	DC Current Gain	I_C= 0.45A; V_{CE}= 3V	25	35		